ADS7029-Q1小型低功耗 8 位、2MSPS SAR ADC

1 特性

- 适用于汽车电子 应用
- 具有符合 AEC-Q100 标准的下列结果：
  - 器件温度 1 级：-40°C 至 125°C 的环境运行温度范围
  - 器件人体放电模型 (HBM) 静电放电 (ESD) 分类等级 ±2000V
  - 器件带电器件模型 (CDM) 静电放电 (ESD) 分类等级 ±1000V
- 超低功耗：
  - 2MSPS、AVDD 为 3V 时的功耗为 1.11 mW（最大值）
  - 1kSPS、AVDD 为 3V 时的功耗低于 1µW
- 微型封装：
  - 8 引脚超薄小外形尺寸 (VSSOP) 封装：2.30mm × 2.00mm
- 吞吐量为 2MSPS 且零延迟
- 宽工作电压范围：
  - AVDD：2.35V 至 3.6V
  - DVDD：1.65V 至 3.6V（与 AVDD 无关）
  - 温度范围：-40°C 至 +125°C
- 性能优异：
  - 8 位分辨率且无丢码 (NMC)
  - ±0.2 最低有效位 (LSB) 微分非线性 (DNL)；±0.25 最低有效位 (LSB) 积分非线性 (INL)
  - 信噪比 (SNR) 为 49dB（3V AVDD 时）
  - 总谐波失真 (THD) 为 -70dB（3V AVDD 时）
- 单极输入范围：0V 至 AVDD
- 集成偏移校准
- 兼容 SPI 的串行接口：32MHz
- 符合 JESD8-7A 标准的数字 I/O

2 应用

- 车用信息娱乐
- 车用传感器
- 液位传感器
- 超声波流量计
- 电机控制
- 便携式医疗设备

3 说明

ADS7029-Q1器件是一款符合汽车类 Q100 标准的 8 位、2MSPS 模数转换器 (ADC)。此器件支持宽范围的模拟输入电压（2.35V 至 3.6V），并且包括一个基于电容器且内置采样保持电路的 SAR ADC。串行外设接口 (SPI) 兼容串口由 $\overline{CS}$ 和 SCLK 信号控制。输入信号在 $\overline{CS}$ 下降沿进行采样，SCLK 用于转换和串行数据输出。此器件支持宽范围的数字电源（1.65V 至 3.6V），可直接连接到各类主机控制器。ADS7029-Q1符合 JESD8-7A 标准的标称 DVDD 范围（1.65V 至 1.95V）。

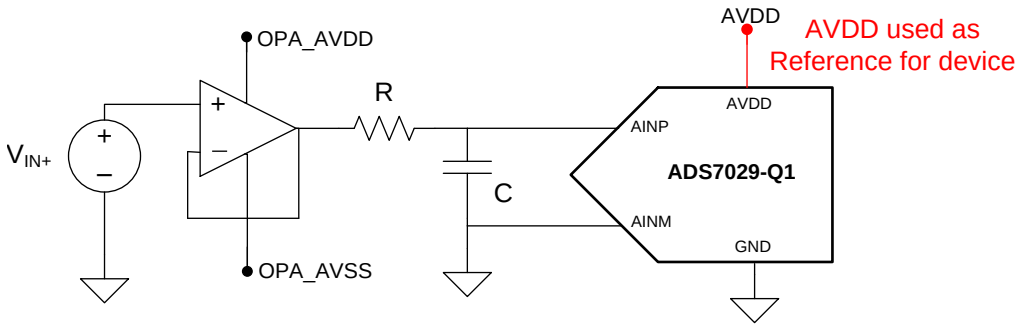
ADS7029-Q1采用 8 引脚微型超薄小外形尺寸 (VSSOP) 封装，额定工作温度范围为 –40°C 至 +125°C。ADS7029-Q1采样速率较快，采用微型封装并具有低功耗特性，适用于空间受限的汽车类快速扫描 标准的理想选择。

器件信息(1)

部件名称	封装	封装尺寸（标称值）
ADS7029-Q1	超薄小外形尺寸封装 (VSSOP)(8)	2.30mm x 2.00mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

典型应用



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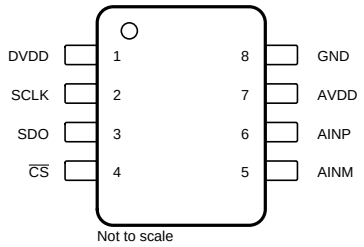
4 修订历史记录

日期	修订版本	注释
2017 年 1 月	*	最初发布。

5 Pin Configuration and Functions

DCU Package
8-Pin Leaded VSSOP
Top View



Not to scale

Pin Functions

NAME	NO.	I/O	DESCRIPTION
AINM	5	Analog input	Analog signal input, negative
AINP	6	Analog input	Analog signal input, positive
AVDD	7	Supply	Analog power-supply input, also provides the reference voltage to the ADC
$\overline{CS}$	4	Digital input	Chip-select signal, active low
DVDD	1	Supply	Digital I/O supply voltage
GND	8	Supply	Ground for power supply, all analog and digital signals are referred to this pin
SCLK	2	Digital input	Serial clock
SDO	3	Digital output	Serial data out

6 Specifications

6.1 Absolute Maximum Ratings(1)

	MIN	MAX	UNIT
AVDD to GND	–0.3	3.9	V
DVDD to GND	–0.3	3.9	V
AINP to GND	–0.3	AVDD + 0.3	V
AINM to GND	–0.3	0.3	V
Digital input voltage to GND	–0.3	DVDD + 0.3	V
Storage temperature, T_{stg}	–60	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002(1)	±2000	V
		Charged-device model (CDM), per AEC Q100-011	±1000	

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
AVDD	Analog supply voltage range	2.35		3.6	V
DVDD	Digital supply voltage range	1.65		3.6	V
T_A	Operating free-air temperature	–40		125	°C

6.4 Thermal Information

THERMAL METRIC(1)		ADS7029-Q1 DCU (VSSOP) 8 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	181.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	50.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	73.9	°C/W
ψ_{JT}	Junction-to-top characterization parameter	1.0	°C/W
ψ_{JB}	Junction-to-board characterization parameter	73.9	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

at T_A = –40°C to 125°C, AVDD = 3 V, DVDD = 1.65 V to 3.6 V, f_{SAMPLE} = 2 MSPS, and V_{AINM} = 0 V (unless otherwise noted)

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
ANALOG INPUT							
	Full-scale input voltage span (1)			0		AVDD	V
	Absolute input voltage range	AINP to GND		–0.1		AVDD + 0.1	V
		AINM to GND		–0.1		0.1	
C_S	Sampling capacitance				15		pF
SYSTEM PERFORMANCE							
	Resolution				8		Bits
NMC	No missing codes			8			Bits
INL	Integral nonlinearity		AVDD = 3 V	–0.5	±0.25	0.5	LSB (2)
DNL	Differential nonlinearity		AVDD = 3 V	–0.4	±0.2	0.4	LSB
E_O	Offset error				±0.5		LSB
dV_{OS}/dT	Offset error drift with temperature				±25		ppm/°C
E_G	Gain error		AVDD = 3 V		±0.2		%FS
	Gain error drift with temperature		No calibration		±25		ppm/°C
SAMPLING DYNAMICS							
t_{ACQ}	Acquisition time			120			ns
	Maximum throughput rate		32-MHz SCLK, AVDD = 2.35 V to 3.6 V			2	MHz
DYNAMIC CHARACTERISTICS							
SNR	Signal-to-noise ratio (3)		f_{IN} = 2 kHz, AVDD = 3 V	48.5	49		dB
THD	Total harmonic distortion (3) (4)		f_{IN} = 2 kHz, AVDD = 3 V		–70		dB
SINAD	Signal-to-noise and distortion (3)		f_{IN} = 2 kHz, AVDD = 3 V	48.5	49		dB
SFDR	Spurious-free dynamic range (3)		f_{IN} = 2 kHz, AVDD = 3 V		75		dB
$BW_{(fp)}$	Full-power bandwidth		At –3 dB, AVDD = 3 V		25		MHz
DIGITAL INPUT/OUTPUT (CMOS Logic Family)							
V_{IH}	High-level input voltage (5)			0.65 × DVDD		DVDD + 0.3	V
V_{IL}	Low-level input voltage (5)			–0.3		0.35 × DVDD	V
V_{OH}	High-level output voltage (5)		At I_{source} = 500 µA	0.8 × DVDD		DVDD	V
			At I_{source} = 2 mA	DVDD – 0.45		DVDD	
V_{OL}	Low-level output voltage (5)		At I_{sink} = 500 µA	0		0.2 × DVDD	V
			At I_{sink} = 2 mA	0		0.45	
POWER-SUPPLY REQUIREMENTS							
AVDD	Analog supply voltage			2.35	3	3.6	V
DVDD	Digital I/O supply voltage			1.65	3	3.6	V
I_{AVDD}	Analog supply current		At 2 MSPS with AVDD = 3 V		335	370	µA
I_{DVDD}	Digital supply current		AVDD = 3 V, no load, no transitions		10		µA
P_D	Power dissipation		At 2 MSPS with AVDD = 3 V		1.005	1.11	mW

(1) Ideal input span; does not include gain or offset error.
(2) LSB means least significant bit.
(3) All specifications expressed in decibels (dB) refer to the full-scale input (FSR) and are tested with an input signal 0.5 dB below full-scale, unless otherwise specified.
(4) Calculated on the first nine harmonics of the input frequency.
(5) Digital voltage levels comply with the JESD8-7A standard for DVDD from 1.65 V to 1.95 V; see the *Digital Voltage Levels* section for more details.

6.6 Timing Requirements

all specifications are at T_A = –40°C to 125°C, AVDD = 2.35 V to 3.6 V, DVDD = 1.65 V to 3.6 V, and C_{LOAD} on SDO = 20 pF (unless otherwise specified)

		MIN	TYP	MAX	UNIT
t_{ACQ}	Acquisition time	120			ns
f_{SCLK}	SCLK frequency	0.016		24	MHz
t_{SCLK}	SCLK period	41.67			ns
t_{PH_CK}	SCLK high time	0.45		0.55	t_{SCLK}
t_{PL_CK}	SCLK low time	0.45		0.55	t_{SCLK}
t_{PH_CS}	$\overline{CS}$ high time	30			ns
t_{SU_CSCK}	Setup time: $\overline{CS}$ falling to SCLK falling	12			ns
t_{D_CKCS}	Delay time: last SCLK falling to $\overline{CS}$ rising	10			ns

6.7 Switching Characteristics

all specifications are at T_A = –40°C to 125°C, AVDD = 2.35 V to 3.6 V, DVDD = 1.65 V to 3.6 V, and C_{LOAD} on SDO = 20 pF (unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$f_{THROUGHPUT}$	Throughput				2	MSPS
t_{CYCLE}	Cycle time		0.5			µs
t_{CONV}	Conversion time				$8.5 \times t_{SCLK} + t_{SU\_CSCK}$	ns
t_{DV_CSDO}	Delay time: $\overline{CS}$ falling to data enable				10	ns
t_{D_CKDO}	Delay time: SCLK falling to (next) data valid on DOUT	AVDD = 2.35 V to 3.6 V			25	ns
t_{DZ_CSDO}	Delay time: $\overline{CS}$ rising to DOUT going to tri-state		5			ns

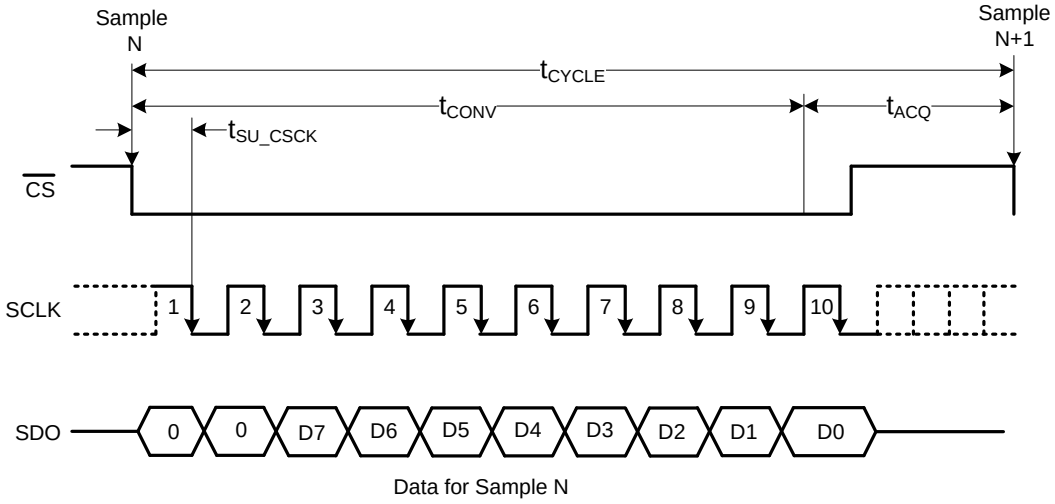
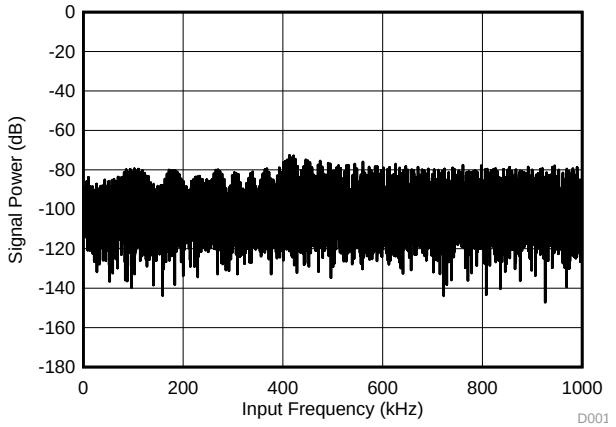


Figure 1. Timing Diagram

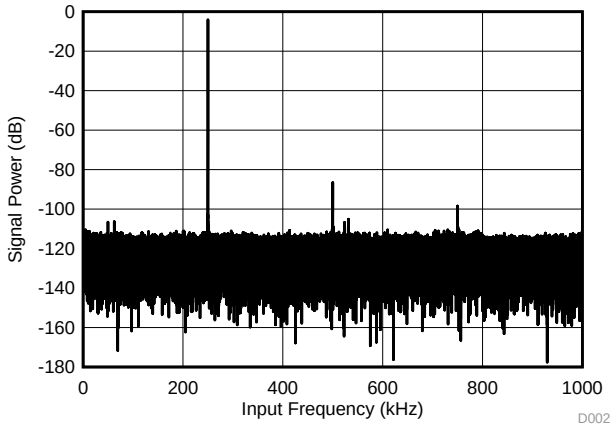
6.8 Typical Characteristics

at T_A = 25°C, AVDD = 3 V, DVDD = 1.8 V, and f_{SAMPLE} = 2 MSPS (unless otherwise noted)



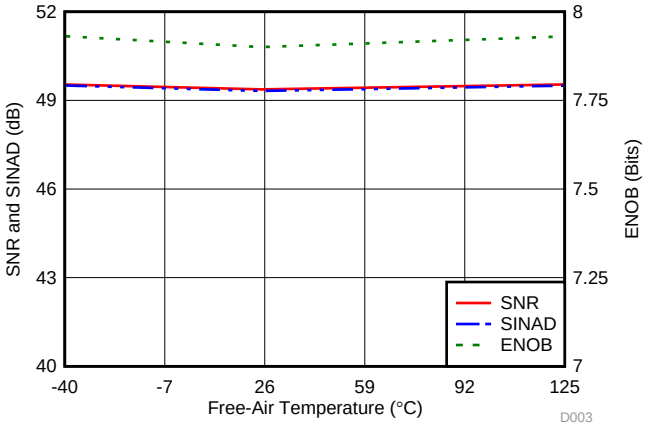
SNR = 49.65 dB, THD = –73.26 dB, f_{IN} = 2 kHz, AVDD = 3 V

Figure 2. Typical FFT



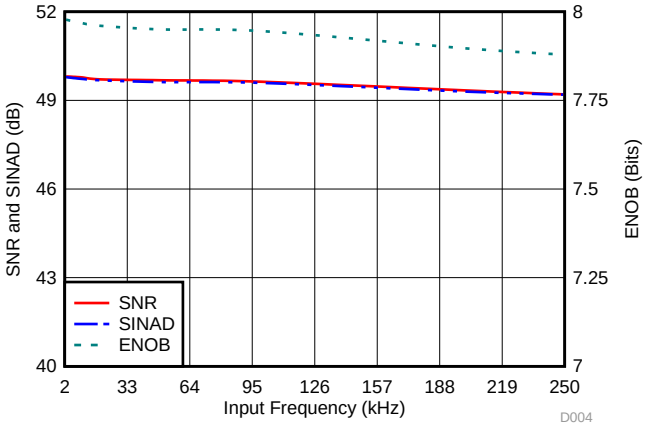
SNR = 49.19 dB, THD = –71.25 dB, f_{IN} = 250 kHz, AVDD = 3 V

Figure 3. Typical FFT



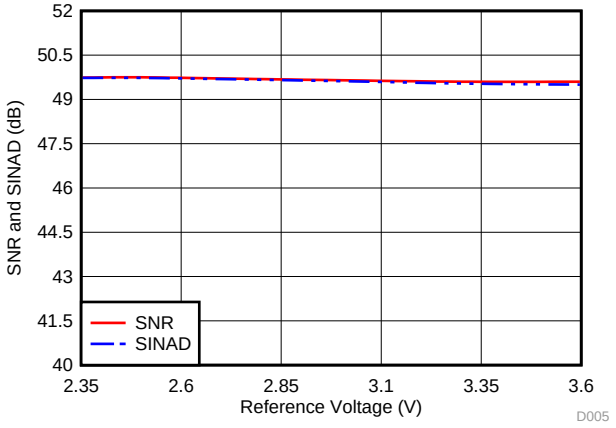
f_{IN} = 2 kHz, AVDD = 3 V

Figure 4. SNR and SINAD vs Temperature



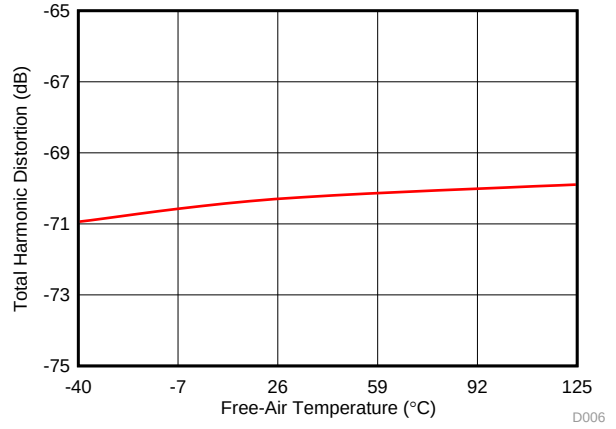
AVDD = 3 V

Figure 5. SNR and SINAD vs Input Frequency



f_{IN} = 2 kHz

Figure 6. SNR and SINAD vs Reference Voltage (AVDD)

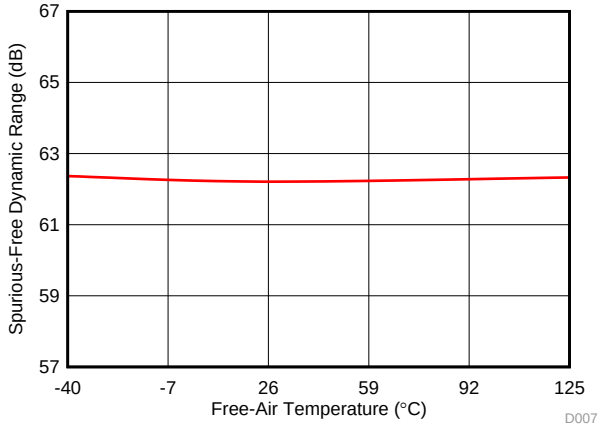


f_{IN} = 2 kHz, AVDD = 3 V

Figure 7. THD vs Temperature

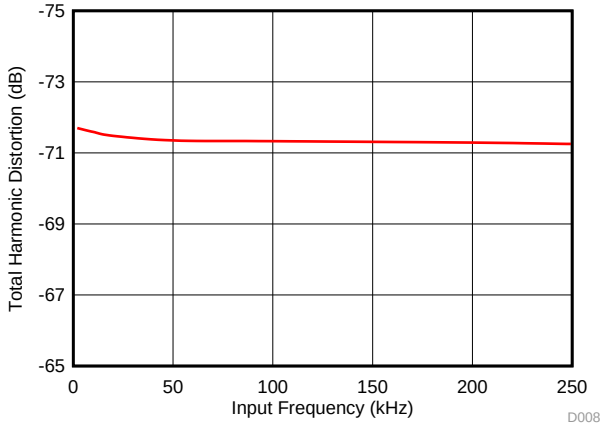
Typical Characteristics (continued)

at T_A = 25°C, AVDD = 3 V, DVDD = 1.8 V, and f_{SAMPLE} = 2 MSPS (unless otherwise noted)



f_{IN} = 2 kHz, AVDD = 3 V

Figure 8. SFDR vs Temperature



AVDD = 3 V

Figure 9. THD vs Input Frequency

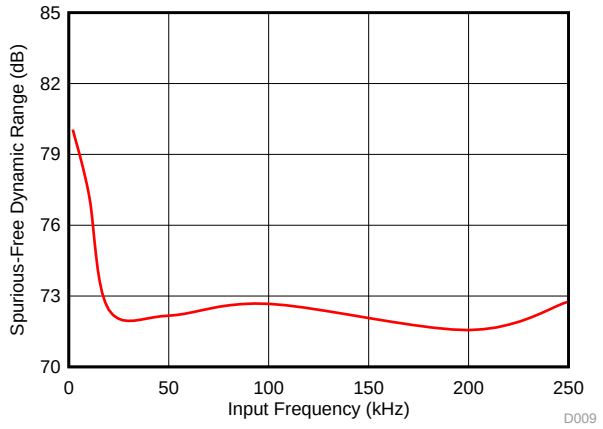
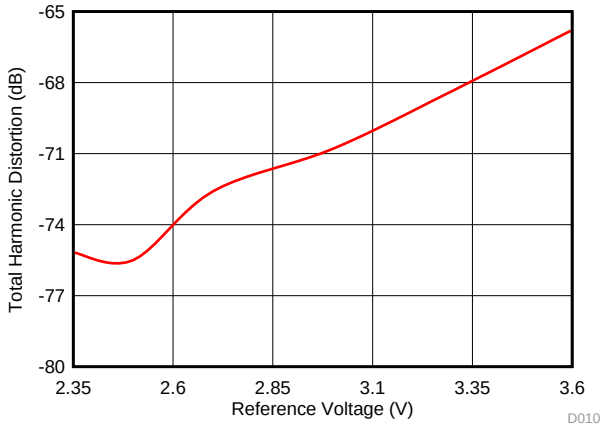
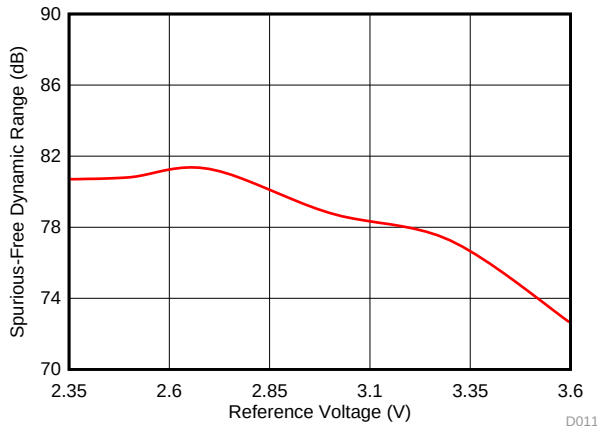


Figure 10. SFDR vs Input Frequency



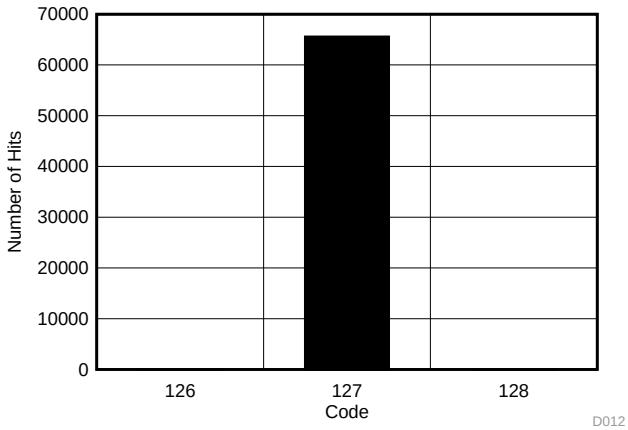
f_{IN} = 2 kHz, AVDD = 3 V

Figure 11. THD vs Reference Voltage (AVDD)



f_{IN} = 2 kHz, AVDD = 3 V

Figure 12. SFDR vs Reference Voltage (AVDD)

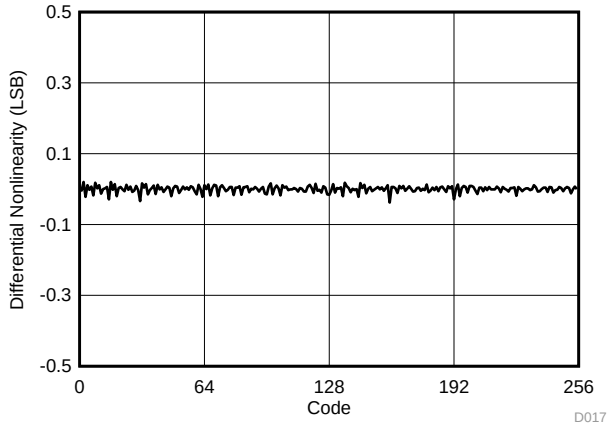


Mean code = 127, sigma = 0, AVDD = 3 V

Figure 13. DC Input Histogram

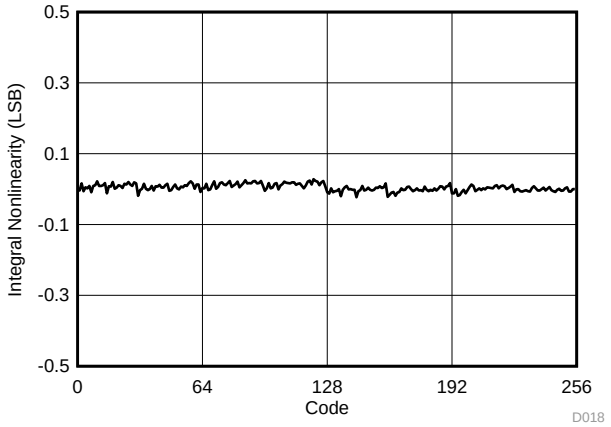
Typical Characteristics (continued)

at T_A = 25°C, AVDD = 3 V, DVDD = 1.8 V, and f_{SAMPLE} = 2 MSPS (unless otherwise noted)



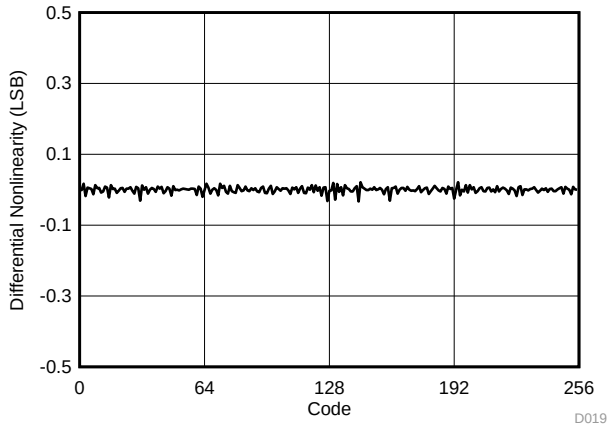
AVDD = 2.35 V

Figure 14. Typical DNL



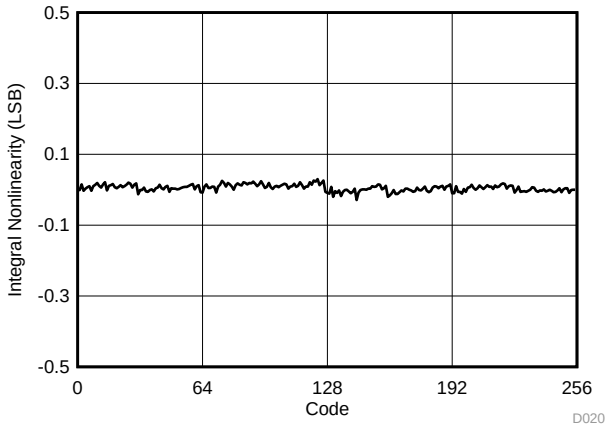
AVDD = 2.35 V

Figure 15. Typical INL



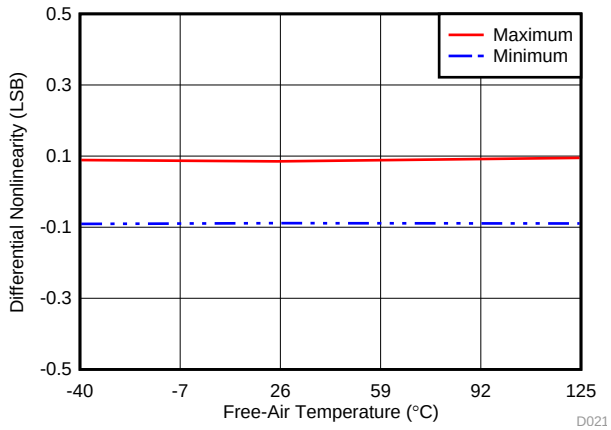
AVDD = 3 V

Figure 16. Typical DNL



AVDD = 3 V

Figure 17. Typical INL



AVDD = 3 V

Figure 18. DNL vs Temperature

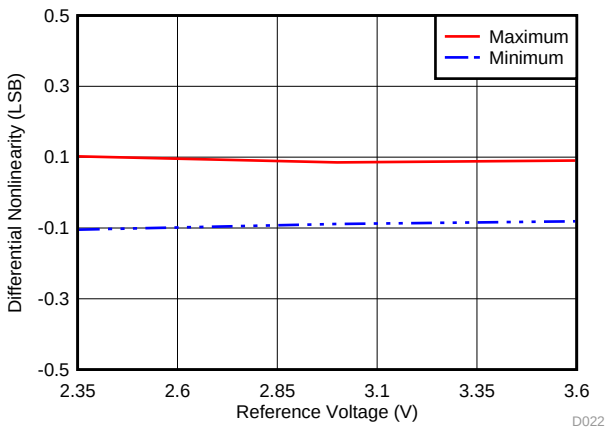
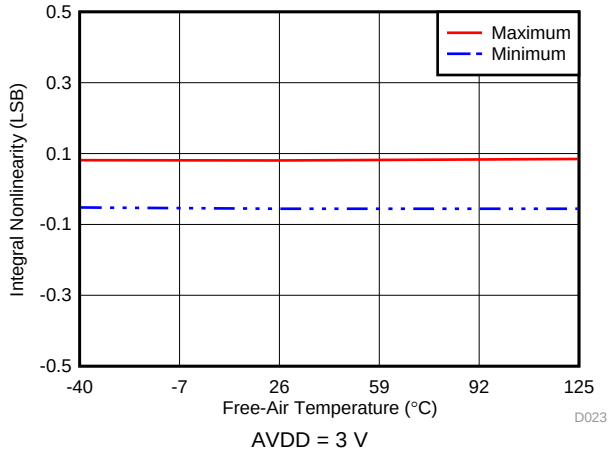


Figure 19. DNL vs Reference Voltage (AVDD)

Typical Characteristics (continued)

at T_A = 25°C, AVDD = 3 V, DVDD = 1.8 V, and f_{SAMPLE} = 2 MSPS (unless otherwise noted)



AVDD = 3 V

Figure 20. INL vs Temperature

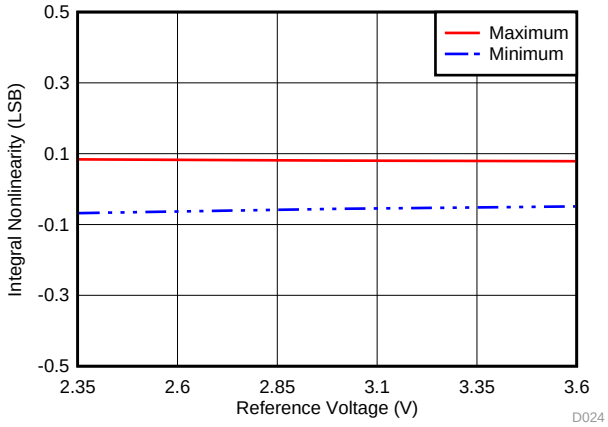
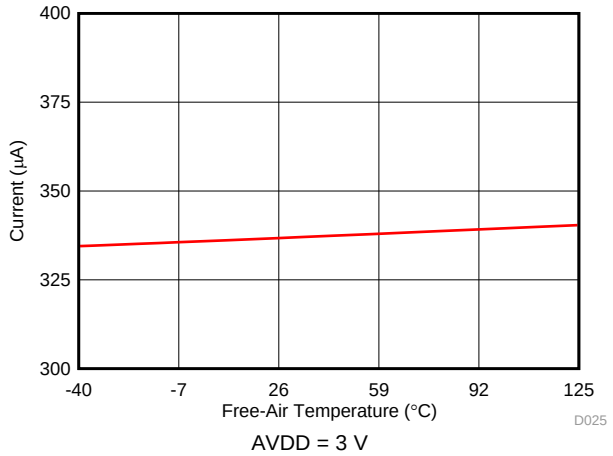
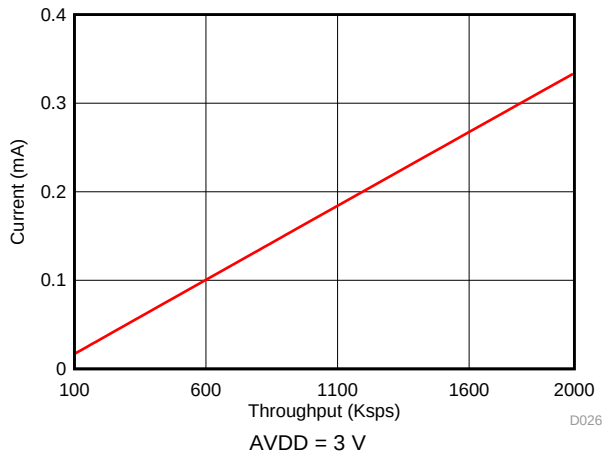


Figure 21. INL vs Reference Voltage (AVDD)



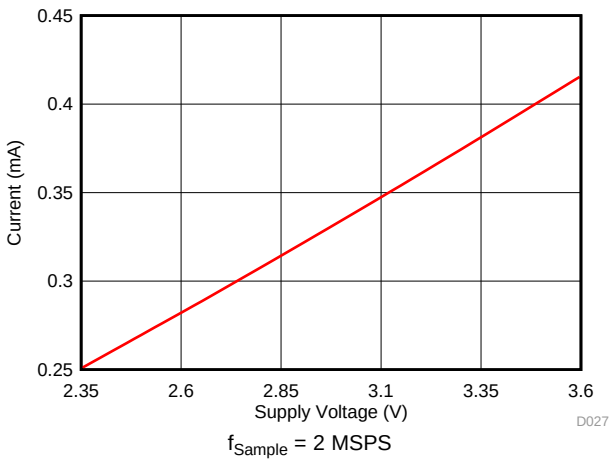
AVDD = 3 V

Figure 22. AVDD Supply Current vs Temperature



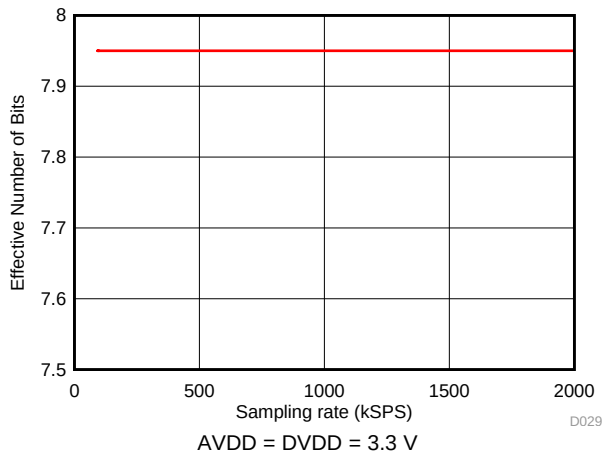
AVDD = 3 V

Figure 23. AVDD Supply Current vs Throughput



f_{Sample} = 2 MSPS

Figure 24. AVDD Supply Current vs Supply Voltage



AVDD = DVDD = 3.3 V

Figure 25. ENOB vs Sampling Rate

Typical Characteristics (continued)

at T_A = 25°C, AVDD = 3 V, DVDD = 1.8 V, and f_{SAMPLE} = 2 MSPS (unless otherwise noted)

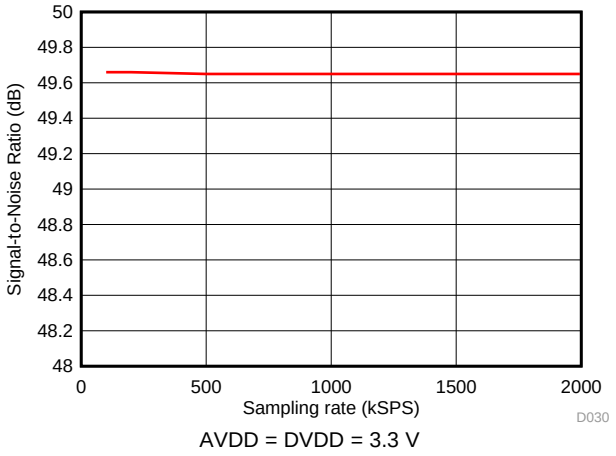


Figure 26. SNR vs Sampling Rate

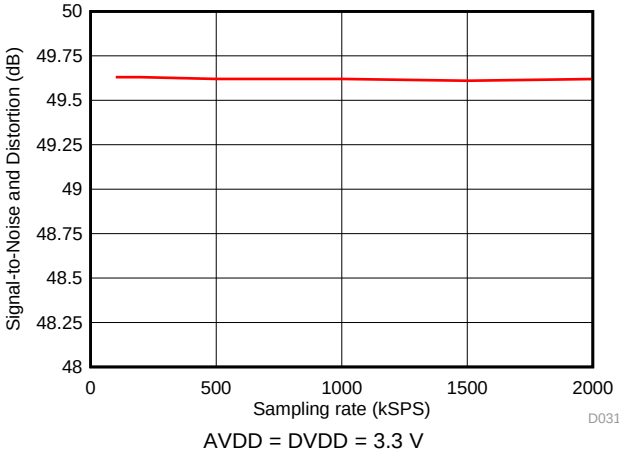


Figure 27. SINAD vs Sampling Rate

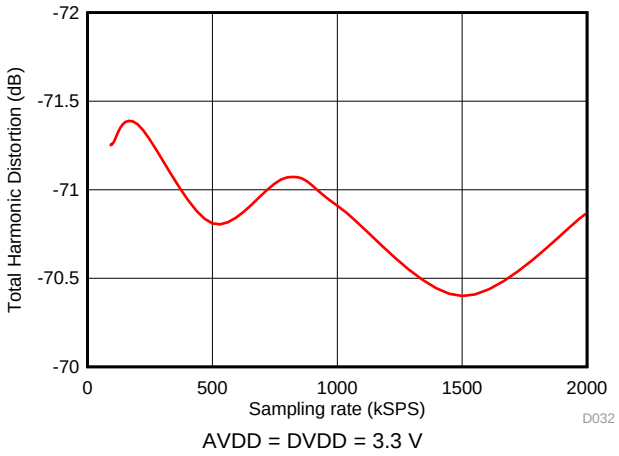


Figure 28. THD vs Sampling Rate

7 Parameter Measurement Information

7.1 Digital Voltage Levels

The device complies with the JESD8-7A standard for DVDD from 1.65 V to 1.95 V. Figure 29 shows voltage levels for the digital input and output pins.

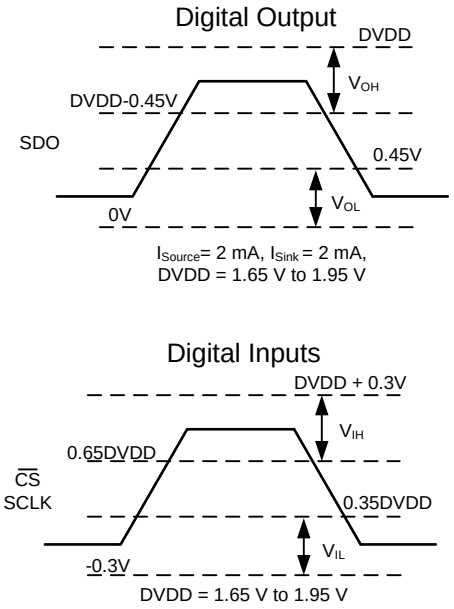


Figure 29. Digital Voltage Levels as per the JESD8-7A Standard

8 Detailed Description

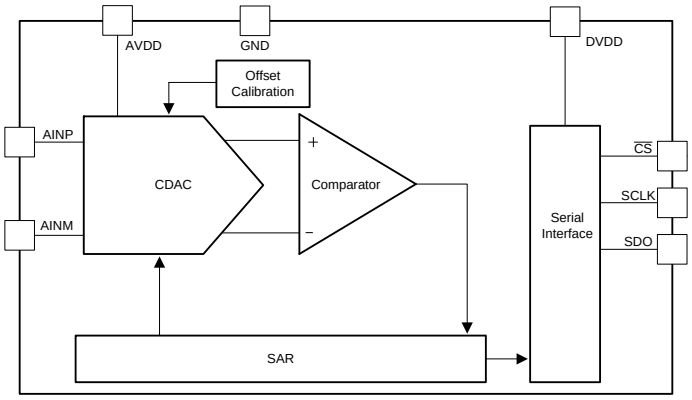
8.1 Overview

The ADS7029-Q1 is an ultra-low-power, miniature analog-to-digital converter (ADC) that supports a wide analog input range. The analog input range for the device is defined by the AVDD supply voltage. The device samples the input voltage across the AINP and AINM pins on the $\overline{CS}$ falling edge and starts the conversion. The clock provided on the SCLK pin is used for conversion and data transfer. During conversions, both the AINP and AINM pins are disconnected from the sampling circuit. After the conversion completes, the sampling capacitors are reconnected across the AINP and AINM pins and the ADS7029-Q1 enters acquisition phase.

The device has an internal offset calibration. The offset calibration can be initiated by the user either on power-up or during normal operation; see the *Offset Calibration* section for more details.

The device also provides a simple serial interface to the host controller and operates over a wide range of digital power supplies. The ADS7029-Q1 requires only a 24-MHz SCLK for supporting a throughput of 2 MSPS. The digital interface also complies with the JESD8-7A (normal range) standard. The *Functional Block Diagram* section provides a block diagram of the device.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Reference

The device uses the analog supply voltage (AVDD) as a reference, as shown in Figure 30. The AVDD pin is recommended to be decoupled with a 3.3-µF, low equivalent series resistance (ESR) ceramic capacitor.. The AVDD pin functions as a switched capacitor load to the source powering AVDD. The decoupling capacitor provides the instantaneous charge required by the internal circuit and helps in maintaining a stable dc voltage on the AVDD pin. The AVDD pin is recommended to be powered with a low output impedance and low-noise regulator (such as the TPS73230).

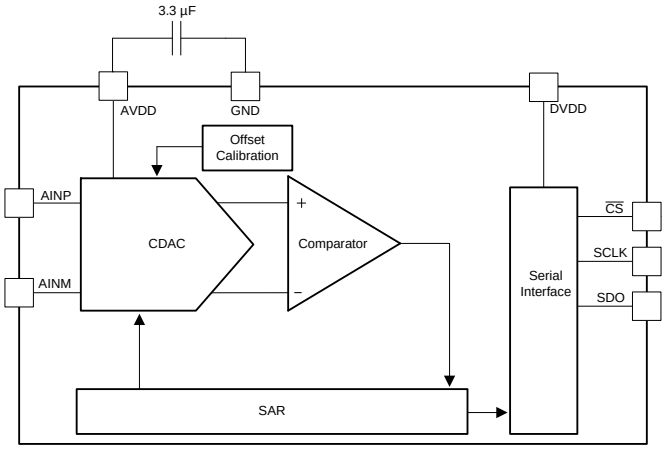


Figure 30. Reference for the Device

Feature Description (continued)

8.3.2 Analog Input

The device supports single-ended analog inputs. The ADC samples the difference between AINP and AINM and converts for this voltage. The device is capable of accepting a signal from –100 mV to 100 mV on the AINM input and is useful in systems where the sensor or signal-conditioning block is far from the ADC. In such a scenario, there can be a difference between the ground potential of the sensor or signal conditioner and the ADC ground. In such cases, use separate wires to connect the ground of the sensor or signal conditioner to the AINM pin. The AINP input is capable of accepting signals from 0 V to AVDD. Figure 31 represents the equivalent analog input circuits for the sampling stage. The device has a low-pass filter followed by the sampling switch and sampling capacitor. The sampling switch is represented by an R_S (typically 50 Ω) resistor in series with an ideal switch and C_S (typically 15 pF) is the sampling capacitor. The ESD diodes are connected from both analog inputs to AVDD and ground.

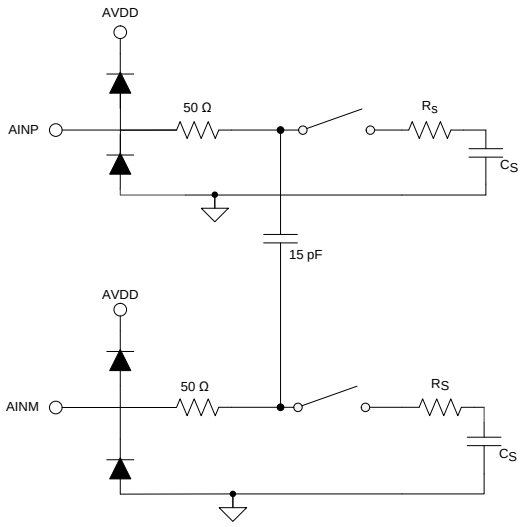


Figure 31. Equivalent Input Circuit for the Sampling Stage

The analog input full-scale range (FSR) is equal to the reference voltage of the ADC. The reference voltage for the device is equal to the analog supply voltage (AVDD). Thus, the device FSR can be determined by Equation 1:

$$FSR = V_{REF} = AVDD \quad (1)$$

Feature Description (continued)

8.3.3 ADC Transfer Function

The device output is in straight binary format. The device resolution for a single-ended input can be computed by Equation 2:

$$1\ LSB = V_{REF} / 2^N \quad (2)$$

where:

- V_{REF} = AVDD and
- N = 8

Figure 32 and Table 1 show the ideal transfer characteristics for the device.

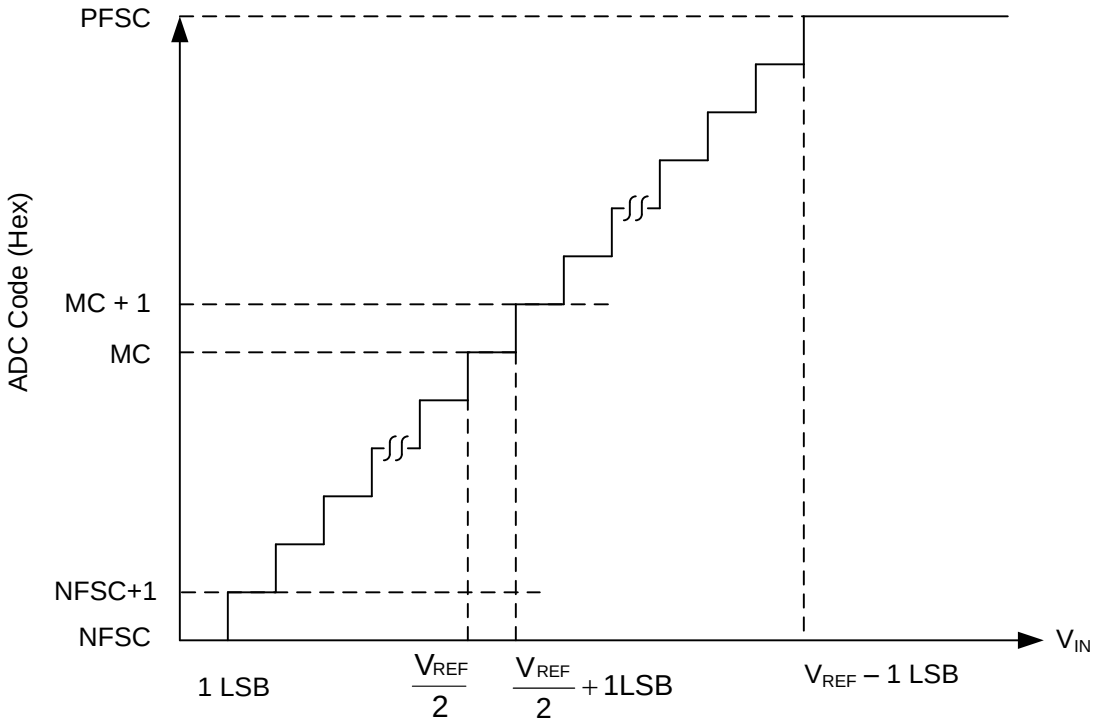


Figure 32. Ideal Transfer Characteristics

Table 1. Transfer Characteristics

INPUT VOLTAGE (AINP – AINM)	CODE	DESCRIPTION	IDEAL OUTPUT CODE (HEX)
≤1 LSB	NFSC	Negative full-scale code	00
1 LSB to 2 LSBs	NFSC + 1	—	01
(V_{REF} / 2) to (V_{REF} / 2) + 1 LSB	MC	Mid code	80
(V_{REF} / 2) + 1 LSB to (V_{REF} / 2) + 2 LSBs	MC + 1	—	81
≥ V_{REF} – 1 LSB	PFSC	Positive full-scale code	FF

8.3.4 Serial Interface

The device supports a simple, SPI-compatible interface to the external host. The $\overline{CS}$ signal defines one conversion and serial transfer frame. A frame starts with a $\overline{CS}$ falling edge and ends with a $\overline{CS}$ rising edge. The SDO pin outputs the ADC conversion results. Figure 33 shows a detailed timing diagram for the serial interface. A minimum delay of t_{SU_CSCK} must elapse between the $\overline{CS}$ falling edge and the first SCLK falling edge. The device uses the clock provided on the SCLK pin for conversion and data transfer. The conversion result is available on the SDO pin with the first two bits set to 0, followed by 12 bits of the conversion result. The first zero is launched on the SDO pin on the $\overline{CS}$ falling edge. Subsequent bits (starting with another 0 followed by the conversion result) are launched on the SDO pin on subsequent SCLK falling edges. The SDO output remains low after 14 SCLKs. A $\overline{CS}$ rising edge ends the frame and brings the serial data bus to tri-state. For acquisition of the next sample, a minimum time of t_{ACQ} must be provided after the conversion of the current sample is completed. For details on timing specifications, see the *Timing Requirements* table.

The device initiates an offset calibration on the first $\overline{CS}$ falling edge after power-up and the SDO output remains low during the first serial transfer frame after power-up. For further details, see the *Offset Calibration* section.

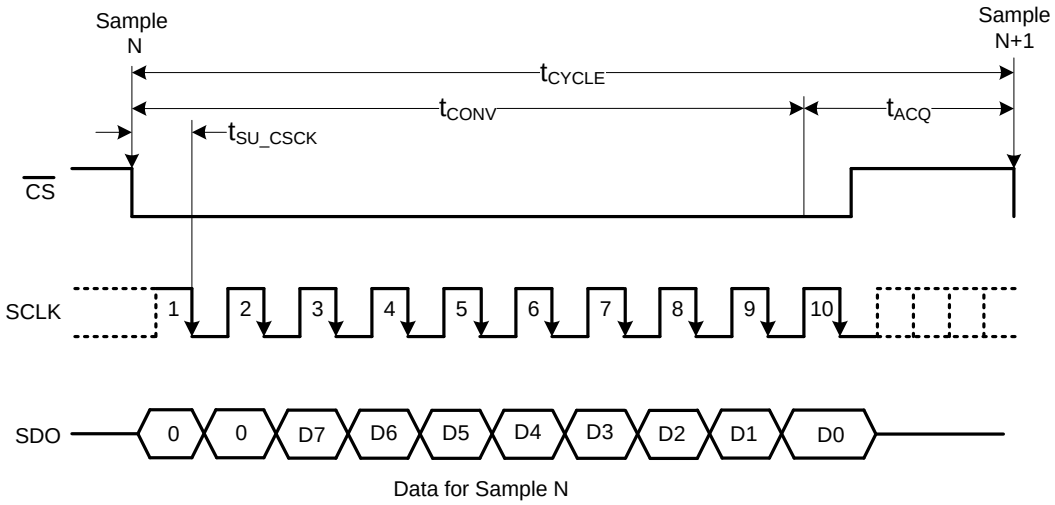
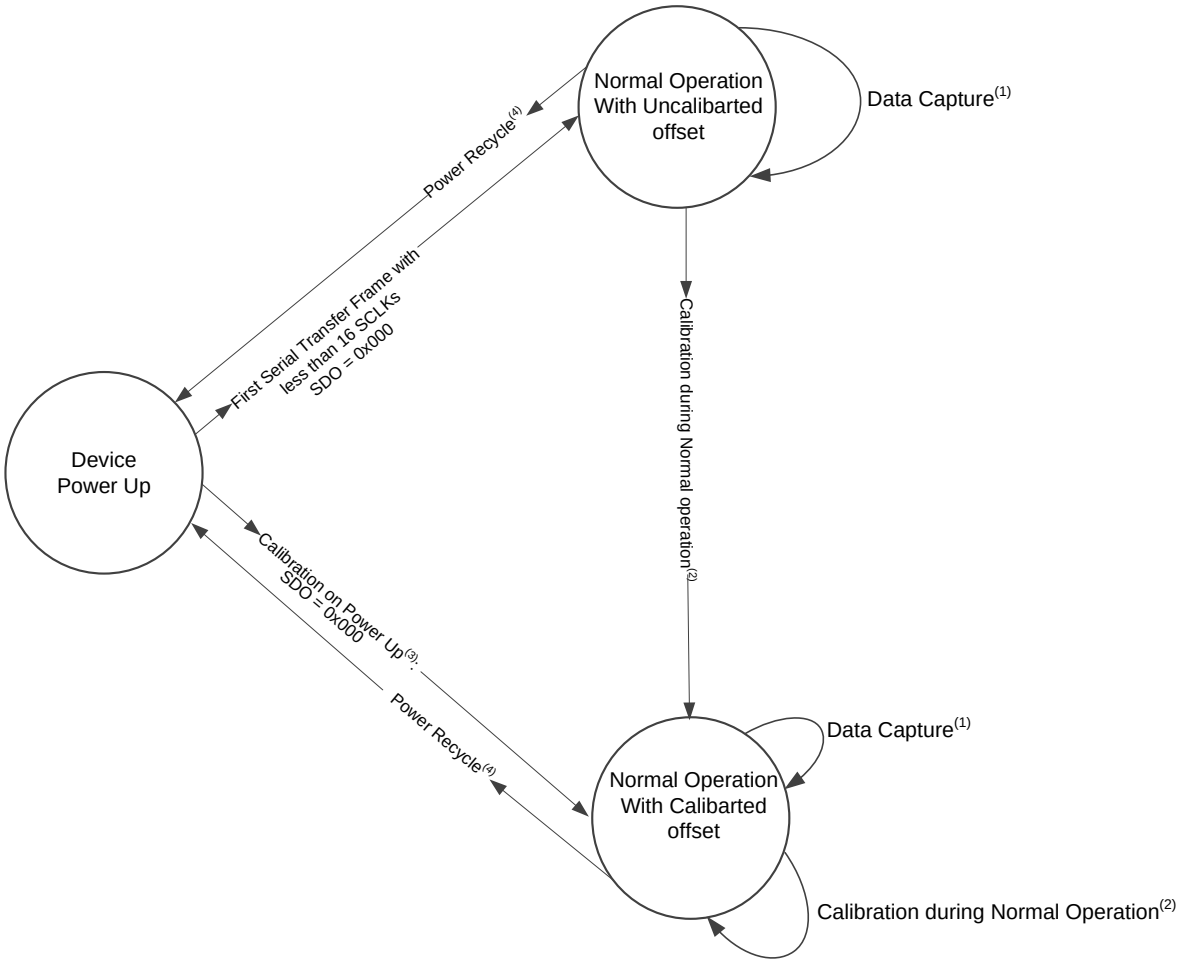


Figure 33. Serial Interface Timing Diagram

8.4 Device Functional Modes

8.4.1 Offset Calibration

The ADS7029-Q1 includes a feature to calibrate the device internal offset. During offset calibration, the analog input pins (AINP and AINM) are disconnected from the sampling stage. The device includes an internal offset calibration register (OCR) that stores the offset calibration result. The OCR is an internal register and cannot be accessed by the user through the serial interface. The OCR is reset to zero on power-up. Therefore, it is recommended to calibrate the offset on power-up in order to bring the offset error within the specified limits. If the operating temperature or analog supply voltage reflect a significant change, the offset can be recalibrated during normal operation. Figure 34 shows the offset calibration process.



(1) See the *Timing Requirements* section for timing specifications.

(2) See the *Offset Calibration During Normal Operation* section for details.

(3) See the *Offset Calibration on Power-Up* section for details.

(4) The power recycle on the AVDD supply is required to reset the offset calibration and to bring the device to a power-up state.

Figure 34. Offset Calibration

Device Functional Modes (continued)

8.4.1.1 Offset Calibration on Power-Up

The device initiates offset calibration on the first $\overline{CS}$ falling edge after power-up and calibration completes if the $\overline{CS}$ pin remains low for at least 16 SCLK falling edges after the first $\overline{CS}$ falling edge. The SDO output remains low during calibration. The minimum acquisition time must be provided after calibration for acquiring the first sample. If the device is not provided with at least 16 SCLKs during the first serial transfer frame after power-up, the OCR is not updated. Table 2 provides the timing parameters for offset calibration on power-up.

For subsequent samples, the device adjusts the conversion results with the value stored in the OCR. The conversion result adjusted with the value stored in OCR is provided by the device on the SDO output. Figure 35 shows the timing diagram for offset calibration on power-up.

Table 2. Offset Calibration on Power-Up

		MIN	TYP	MAX	UNIT
$f_{CLK-CAL}$	SCLK frequency for calibration			12	MHz
$t_{POWERUP-CAL}$	Calibration time at power-up	15 × t_{SCLK}			ns
t_{ACQ}	Acquisition time	120			ns
t_{PH_CS}	$\overline{CS}$ high time	t_{ACQ}			ns
t_{SU_CSCK}	Setup time: $\overline{CS}$ falling to SCLK falling	12			ns
t_{D_CKCS}	Delay time: last SCLK falling to $\overline{CS}$ rising	10			ns

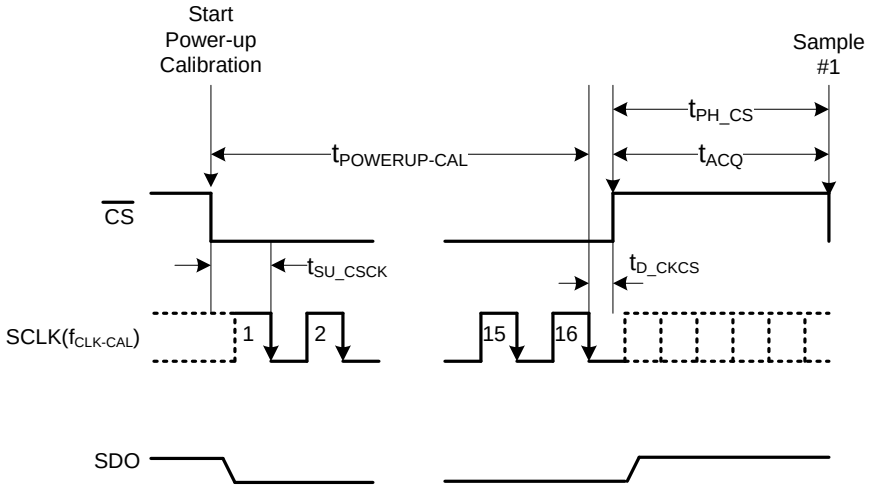


Figure 35. Offset Calibration on Power-Up Timing Diagram

8.4.1.2 Offset Calibration During Normal Operation

Offset calibration can be done during normal device operation if at least 32 SCLK falling edges are provided in one serial transfer frame. During the first 10 SCLKs, the device converts the sample acquired on the $\overline{CS}$ falling edge and provides data on the SDO output. The device initiates the offset calibration on the 17th SCLK falling edge and calibration completes on the 32nd SCLK falling edge. The SDO output remains low after the 10th SCLK falling edge and SDO goes to tri-state after $\overline{CS}$ goes high. If the device is provided with less than 32 SCLKs during a serial transfer frame, the OCR is not updated. Table 3 provides the timing parameters for offset calibration during normal operation.

For subsequent samples, the device adjusts the conversion results with the value stored in the OCR. The conversion result adjusted with the value stored in the OCR is provided by the device on the SDO output. Figure 36 shows the timing diagram for offset calibration during normal operation.

Table 3. Offset Calibration During Normal Operation

		MIN	TYP	MAX	UNIT
$f_{CLK-CAL}$	SCLK frequency for calibration			12	MHz
t_{CAL}	Calibration time during normal operation	15 × t_{SCLK}			ns
t_{ACQ}	Acquisition time	120			ns
t_{PH_CS}	$\overline{CS}$ high time	t_{ACQ}			ns
t_{SU_CSCK}	Setup time: $\overline{CS}$ falling to SCLK falling	12			ns
t_{D_CKCS}	Delay time: last SCLK falling to $\overline{CS}$ rising	10			ns

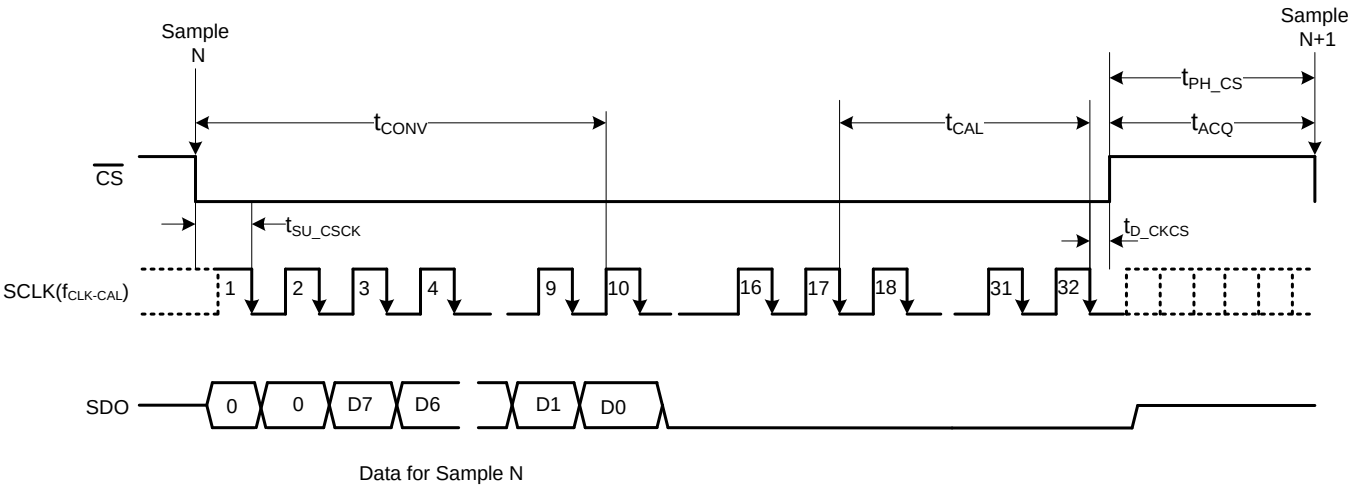


Figure 36. Offset Calibration During Normal Operation Timing Diagram

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The two primary circuits required to maximize the performance of a SAR ADC are the input driver and the reference driver circuits. This section details some general principles for designing the input driver circuit, reference driver circuit, and provides some application circuits designed for the ADS7029-Q1.

9.2 Typical Application

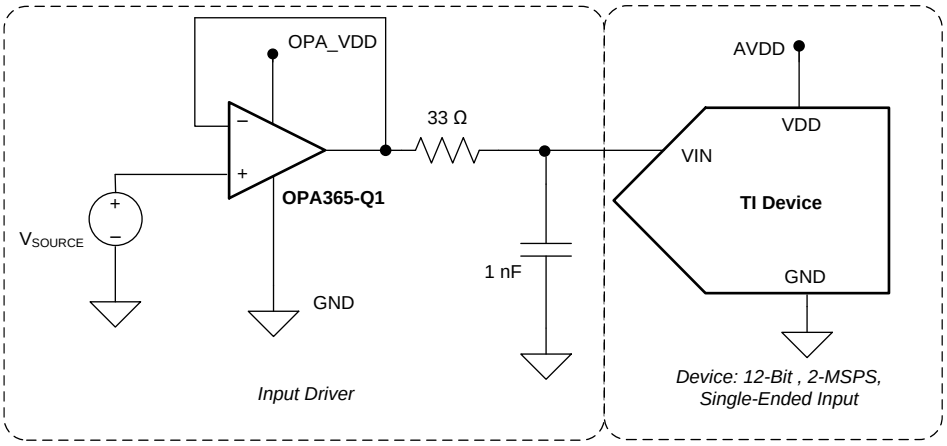


Figure 37. Single-Supply DAQ with the ADS7029-Q1

9.2.1 Design Requirements

The goal of this application is to design a single-supply digital acquisition (DAQ) circuit based on the ADS7029-Q1 with SNR greater than 49 dB and THD less than –70 dB for input frequencies of 2 kHz at a throughput of 2 MSPS.

9.2.2 Detailed Design Procedure

The input driver circuit for a high-precision ADC mainly consists of two parts: a driving amplifier and a charge kickback filter. Careful design of the front-end circuit is critical to meet the linearity and noise performance of a high-precision ADC.

Typical Application (continued)

9.2.2.1 Low Distortion Charge Kickback Filter Design

Figure 38 shows the input circuit of a typical SAR ADC. During the acquisition phase, the SW switch closes and connects the sampling capacitor (C_{SH}) to the input driver circuit. This action introduces a transient on the input pins of the SAR ADC. An ideal amplifier with 0 Ω of output impedance and infinite current drive can settle this transient in zero time. For a real amplifier with non-zero output impedance and finite drive strength, this switched capacitor load can create stability issues.

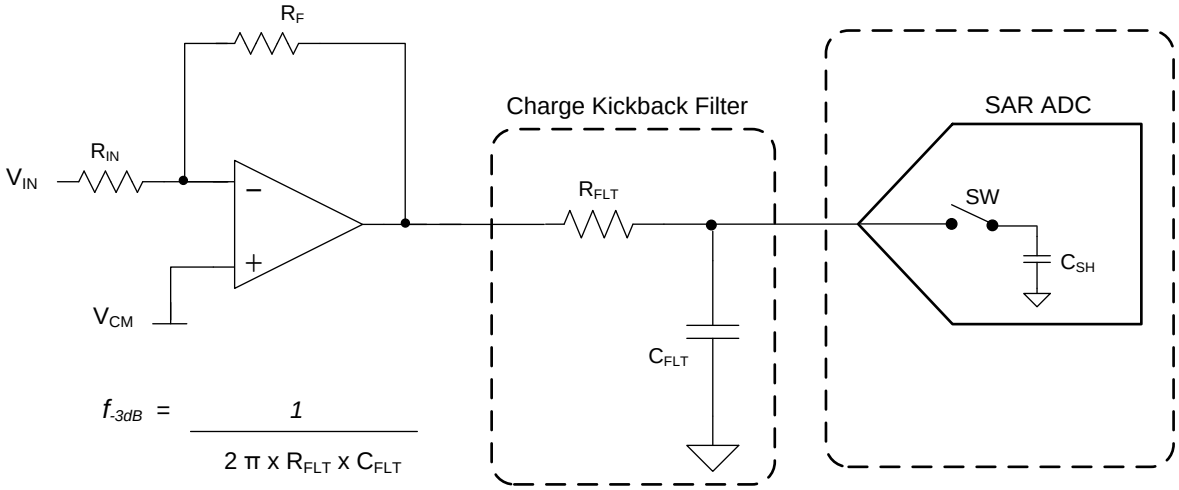


Figure 38. Charge Kickback Filter

For ac signals, the filter bandwidth must be kept low to band limit the noise fed into the ADC input, thereby increasing the SNR of the system. Besides filtering the noise from the front-end drive circuitry, the RC filter also helps attenuate the sampling charge injection from the switched-capacitor input stage of the ADC. A filter capacitor, C_{FLT}, is connected across the ADC inputs. This capacitor helps reduce the sampling charge injection and provides a charge bucket to quickly charge the internal sample-and-hold capacitors during the acquisition process. As a rule of thumb, the value of this capacitor is at least 20 times the specified value of the ADC sampling capacitance. For this device, the input sampling capacitance is equal to 15 pF. Thus, the value of C_{FLT} is greater than 300 pF. Select a COG- or NPO-type capacitor because these capacitor types have a high-Q, low-temperature coefficient, and stable electrical characteristics under varying voltages, frequency, and time.

Note that driving capacitive loads can degrade the phase margin of the input amplifiers, thus making the amplifier marginally unstable. To avoid amplifier stability issues, series isolation resistors (R_{FLT}) are used at the output of the amplifiers. A higher value of R_{FLT} is helpful from the amplifier stability perspective, but adds distortion as a result of interactions with the nonlinear input impedance of the ADC. Distortion increases with source impedance, input signal frequency, and input signal amplitude. Therefore, the selection of R_{FLT} requires balancing the stability and distortion of the design.

The input amplifier bandwidth is typically much higher than the cutoff frequency of the antialiasing filter. Thus, a SPICE simulation is strongly recommended to be performed to confirm that the amplifier has more than 40° phase margin with the selected filter. Simulation is critical because even with high-bandwidth amplifiers, some amplifiers can require more bandwidth than others to drive similar filters.

Typical Application (continued)

9.2.2.2 Input Amplifier Selection

To achieve a SINAD greater than 49 dB, the operational amplifier must have high bandwidth in order to settle the input signal within the acquisition time of the ADC. The operational amplifier must have low noise to keep the total system noise below 20% of the input-referred noise of the ADC. For the application circuit illustrated in Figure 37, the OPA365-Q1 is selected for its high bandwidth (50 MHz) and low noise (4.5 nV/$\sqrt{\text{Hz}}$).

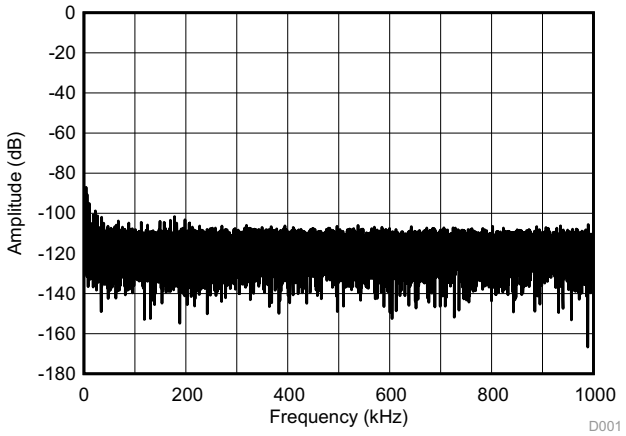
For a step-by-step design procedure for a low-power, small form-factor digital acquisition (DAQ) circuit based on similar SAR ADCs, see the *Three 12-Bit Data Acquisition Reference Designs Optimized for Low Power and Ultra-Small Form Factor* TI Precision Design.

9.2.2.3 Reference Circuit

The analog supply voltage of the device is also used as a voltage reference for conversion. The AVDD pin is recommended to be decoupled with a 3.3-µF, low-ESR ceramic capacitor.

9.2.3 Application Curve

Figure 39 shows the FFT plot for the ADS7029-Q1 with a 2-kHz input frequency used for the circuit in Figure 37.



SNR = 70.6 dB, THD = –86 dB, SINAD = 70.2 dB, number of samples = 32768

Figure 39. Test Results for the ADS7029-Q1 and OPA365-Q1 for a 2-kHz Input

10 Power Supply Recommendations

10.1 AVDD and DVDD Supply Recommendations

The ADS7029-Q1 has two separate power supplies: AVDD and DVDD. The device operates on AVDD; DVDD is used for the interface circuits. AVDD and DVDD can be independently set to any value within the permissible ranges. The AVDD supply also defines the full-scale input range of the device. Always set the AVDD supply to be greater than or equal to the maximum input signal to avoid saturation of codes. Decouple the AVDD and DVDD pins individually with 3.3-µF ceramic decoupling capacitors, as shown in Figure 40.

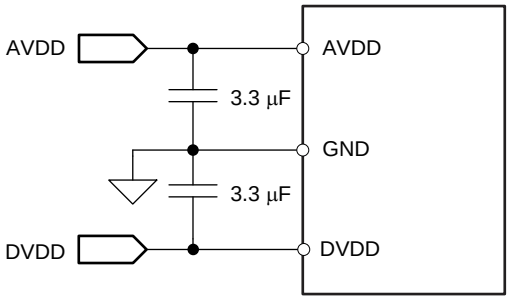


Figure 40. Power-Supply Decoupling

10.2 Estimating Digital Power Consumption

The current consumption from the DVDD supply depends on the DVDD voltage, load capacitance on the SDO line, and the output code. The load capacitance on the SDO line is charged by the current from the SDO pin on every rising edge of the data output and is discharged on every falling edge of the data output. The current consumed by the device from the DVDD supply can be calculated by Equation 3:

$$I_{DVDD} = C \times V \times f \quad (3)$$

where:

- C = Load capacitance on the SDO line
- V = DVDD supply voltage and
- f = Number of transitions on the SDO output

The number of transitions on the SDO output depends on the output code, and thus changes with the analog input. The maximum value of f occurs when data output on SDO change at every SCLK. SDO data changing at every SCLK results in an output code of AAh or 55h. For an output code of AAh or 55h at a 2-MSPS throughput, the frequency of transitions on the SDO output is 8 MHz.

For the current consumption to remain at the lowest possible value, keep the DVDD supply at the lowest permissible value and keep the capacitance on the SDO line as low as possible.

10.3 Optimizing Power Consumed by the Device

- Keep the analog supply voltage (AVDD) as close as possible to the analog input voltage. Set AVDD to be greater than or equal to the analog input voltage of the device.
- Keep the digital supply voltage (DVDD) at the lowest permissible value.
- Reduce the load capacitance on the SDO output.
- Run the device at the optimum throughput. Power consumption reduces with throughput.

11 Layout

11.1 Layout Guidelines

Figure 41 shows a board layout example for the ADS7029-Q1.

Some of the key considerations for an optimum layout with this device are:

- Use a ground plane underneath the device and partition the printed circuit board (PCB) into analog and digital sections.
- Avoid crossing digital lines with the analog signal path and keep the analog input signals and the reference input signals away from noise sources.
- The power sources to the device must be clean and well-bypassed. Use 2.2-µF ceramic bypass capacitors in close proximity to the analog (AVDD) and digital (DVDD) power-supply pins.
- Avoid placing vias between the AVDD and DVDD pins and the bypass capacitors.
- Connect ground pins to the ground plane using short, low-impedance path.
- Place the fly-wheel RC filters components close to the device.

Among ceramic surface-mount capacitors, COG (NPO) ceramic capacitors provide the best capacitance precision. The type of dielectric used in COG (NPO) ceramic capacitors provides the most stable electrical properties over voltage, frequency, and temperature changes.

11.2 Layout Example

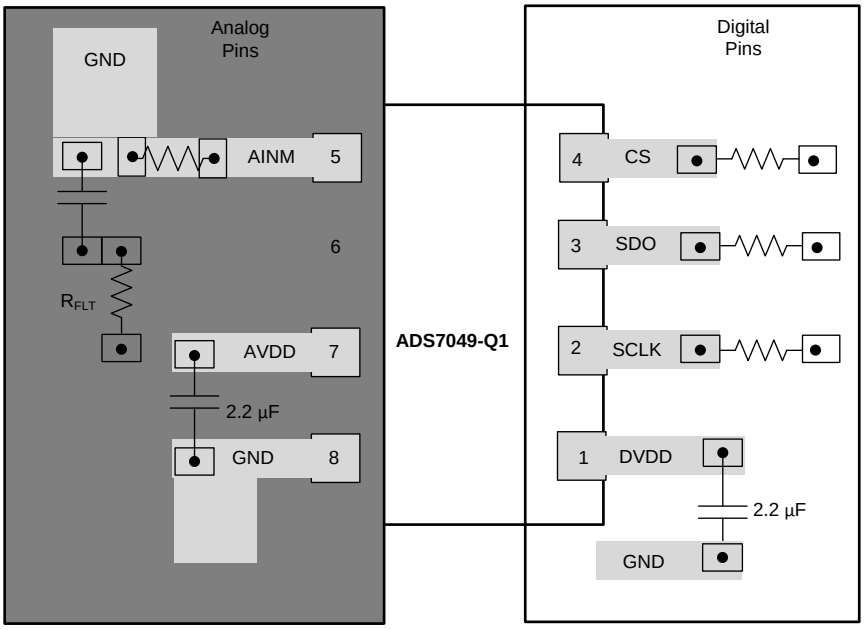


Figure 41. Example Layout

12 器件和文档支持

12.1 文档支持

12.1.1 相关文档

相关文档如下：

- *《TPS732xx 具有反向电流保护功能的无电容 NMOS、250mA 低压降稳压器》*
- *《专为低功耗和超小型特性进行优化的三项 12 位数据采集参考设计》*TI 高精度设计
- *OPAx314 3MHz、低功耗、低噪声、RRIO、1.8V CMOS运算放大器*
- *《OPAx365-Q1 50MHz 低失真、高 CMRR、轨到轨 I/O 单电源运算放大器》*

12.2 接收文档更新通知

如需接收文档更新通知，请访问 www.ti.com.cn 网站上的器件产品文件夹。点击右上角的*提醒我* (Alert me) 注册后，即可每周定期收到已更改的产品信息。有关更改的详细信息，请查阅已修订文档中包含的修订历史记录。

12.3 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 商标

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.5 静电放电警告

ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ADS7029QDCURQ1	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	17TT	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

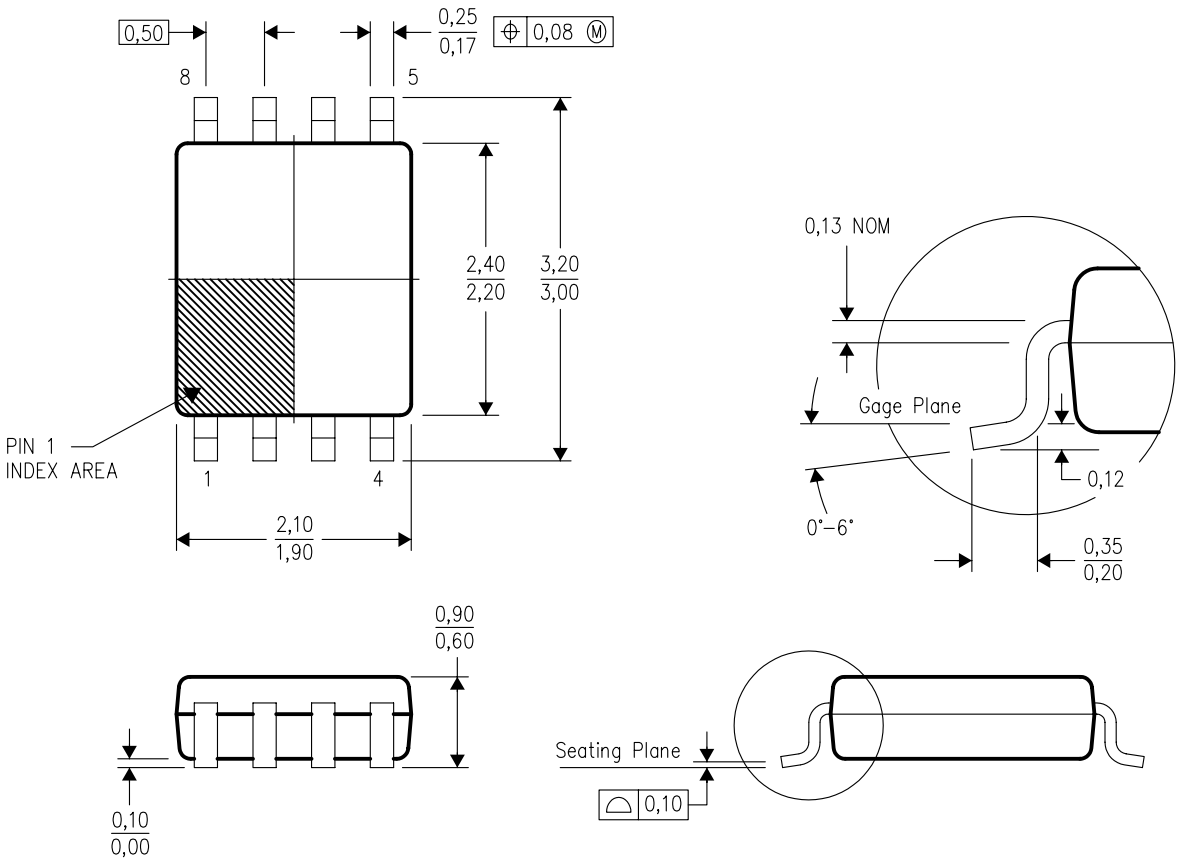
(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

DCU (R–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE (DIE DOWN)



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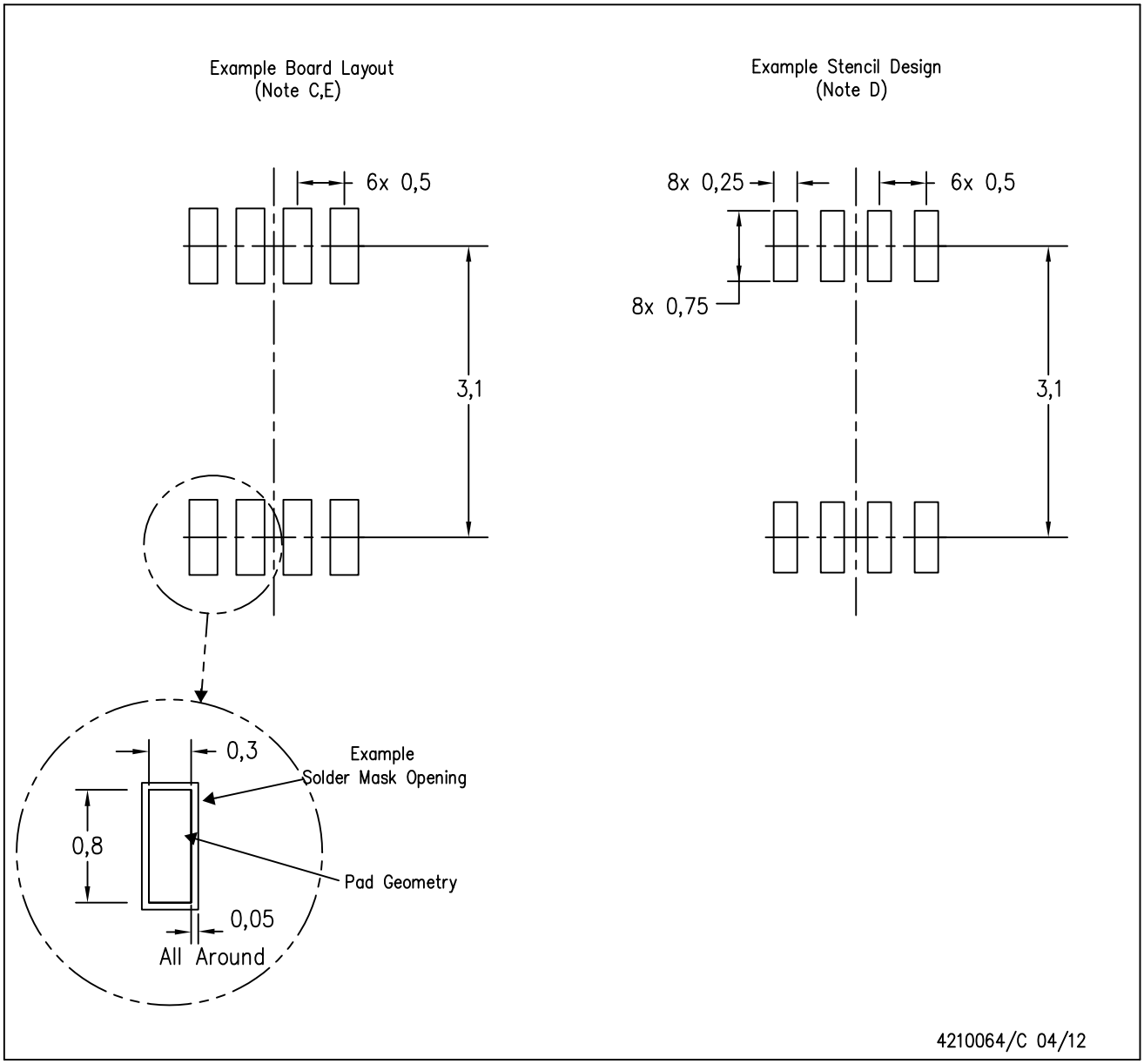
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–187 variation CA.

DCU (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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